

Advanced Power Reports List



Manufacturer	Part #	Report Code	Process Name / Description	Node (µm)	#Metal	#Poly	Supply Vmax	Report Release Date
STMicroelectronics	FSB2D48	PPR-1501-801 FAR-1406-901	BCD9	0.13	5	1	-	Jan-15
Mitsubishi	PSS35S92F6-AG	PPR-1408-901	7th Generation Trench Gate IGBT	1.00	1	1	600V	Jul-14
STMicroelectronics	L9959T	CAR-1407-902	Dual PMOS High-Side H-Bridge (Motor Driver) BiCMOS	0.35	3	1	-	Jul-14
Texas Instruments	BQ24260YFF	PPR-1404-801	LBC8 Bipolar-CMOS-DMOS (BCD)	0.18	3	1	30	May-14
Avago	ACPL-34JT	CAR-1404-903, FAR-1312-903	Gate drive optocoupler BiCMOS	0.25	4	1	-	Apr-14
Infineon	1ED020112F	CAR-1404-901, PPR-1109-902	IGBT Technology	0.80	4	2	-	Mar-14
Infineon	IKW50N65F5FKSA1	PPR-1402-901	TRENCHSTOP™ 5 IGBT	-	2	1	650	Feb-14
Infineon	TLE8718SA	PPR-1310-901	SmartPower BCD	0.50	4	1	-	Dec-13
Toshiba	TJ4FG	CAR-1311-901, FAR-1307-906	IGBT Driver Bipolar	-	2	1	-	Nov-13
Cree	C2M0080120D	PPR-1305-803	2nd Generation Z-FET™	-	-	-	1200	May-13
Renesas	µPD166038T1J	PPR-1305-802	Trench gate power MOSFET + BiCMOS LDMOS- DMOS	mixed	-	-	-	May-13
Qualcomm	PM8921	PPR-1304-802, TCR-1403-901, TCR-1403-902, TCR-1403-903, FAR-1302-901	TSMC 0.18 µm BCDMOS	0.18	5	1	-	Mar-13
Efficient Power Conv.	EPC2012	PPR-1301-802	GaN Power Transistor	-	-	-	200	Jan-13
EPC	EPC2012	PPR-1301-802	GaN enhancement mode power transistor	-	-	-	-	Jan-13
Infineon	TLE98322QVES	PPR-1301-801	Infineon's automotive qualified 130 nm smart power bipolar CMOS-DMOS (BCD)	0.13	-	-	-	Jan-13
Infineon	TLE9832	PPR-1301-801	Smart BCD	0.13	-	-	-	Jan-13
Renesas	RJK0428JWT	PPR-1301-901	N-channel power MOSFET, DC-DC converter	-	-	-	-	Jan-13
Renesas	RJK0428JWT	PPR-1301-901	N-channel Power MOSFET	-	-	-	40	Jan-13
STMicroelectronics	L6390DTR	PPR-1301-803	High-Voltage High/Low-Side Driver BiCMOS/LDMOS	-	-	-	-	Jan-13
Toshiba	TK31J60W	PPR-1212-901	N-channel, super junction, dynamic threshold voltage MOSFET	-	-	-	-	Dec-12

Manufacturer	Part #	Report Code	Process Name / Description	Node (µm)	#Metal	#Poly	Supply Vmax	Report Release Date
Alpha & Omega	AON6716L	EXR-1212-802	N-channel Power MOSFET	-	-	-	30	Dec-12
SiGe Semiconductor	SE2605L	PPR-1211-801	IBM in a 0.35 µm SiGe BiCMOS process that employs TSV technology	0.35	-	-	-	Nov-12
Infineon	IRS21864PBF	PPR-1208-801	power MOSFET and IGBT drivers with independent high-side and low-side referenced output channels	1.00	-	-	-	Aug-12
Mitsubishi	M81738FP	PPR-1207-901	a 1200 V power MOSFET and IGBT module driver for half bridge applications	1	2	2	1200	Jul-12
Atmel	ATA6844	CWR-1203-901	SMART-I.S.	0.80	3	1		Mar-12
International Rectifier	IP2010PBF	PPR-1202-802	Gallium Nitride (GaN)- based power device technology platform	-	-	-	-	Feb-12
Analog Devices	ADUM2200	PPR-1012-905	CMOS Digital Isolator	0.50	3	1		Feb-12
Cree	CMF2012D	EXR-1202-801	SiC MOSFET	-	-	-	1200	Feb-12
International Rectifier	IP2010	PPR-1202-802	GaN High Frequency Power Stage	n/a	3		13.2	Feb-12
International Rectifier	IRS21864	PPR-1201-801	Hi/Lo Side driver	1.00	2	1	600	Jan-12
National Semiconductor	150734-2	PPR-1201-901	BiCMOS (vertical DMOS)	1.5	2	1	-	Jan-12
NXP	TJA1055	PPR-1109-901	BCD-SOI Process	1	3	1	-	Sep-11
Renesas	PS9402	PPR-1109-903	IGBT Technology (BCDMOS, bipolar, GaAs)	0.5	3	2		Sep-11
Atmel	ATA6843	PPR-1108-901	BCD-SOI Process	0.80	3	1		Aug-11
Toshiba	TB9067FNG	CWR-1103-908	BiCMOS / LDMOS	0.6	3	1		Mar-11
Silicon Laboratories	Si8422BD	EXR-1101-801	Isolator	-	-	-	-	Jan-11
STMicroelectronics	ST7570	PPR-1101-801	BCD8	0.18	4	2		Jan-11
NVE	IL715-3E	PPR-1012-903	CMOS Digital Isolator	0.5	3	1	-	Dec-10
Texas Instruments	ISO7220A	PPR-1012-902	BiCMOS	0.7	3	2		Dec-10
Toshiba	TPD4135	PPR-1011-901	BiCMOS on SOI with IGBT	3.5	2	1	500	Nov-10
Efficient Power Conv.	EPC1015	EXR-1005-801	GaN-on-Power Transistor	-	-	-	40	May-10
Freescale	PC900840EP	PPR-0906-901	SMARTMOS10	0.13	4	2		Jun-09
Volterra	THS7530PWP	PPR-0809-801	CMOS-DMOS	0.35	3+RDL	1	5	Sep-08
Power Integrations	TOP250R	CWR-0806-901	BCD	3	1	1	700	Jun-08
NXP	TJA1020	PPR-0709-901	BCD	1.5	2	1	27	Sep-07
International Rectifier	IR1167ASP	CTR-0611-904	BCD	1.00	2	1	18	Nov-06
Silicon Laboratories	Si3400	CTR-0611-910	BCD	1	3	1	57	Nov-06
STMicroelectronics	L6910	CTR-0611-905	BiCMOS	0.8	3	1	12	Nov-06
STMicroelectronics	STA333BW	CTR-0610-901	CMOS-DMOS	0.35	4	1	20	Oct-06

Manufacturer	Part #	Report Code	Process Name / Description	Node (µm)	#Metal	#Poly	Supply Vmax	Report Release Date
National Semiconductor	LMV791	SAR-609-801	BiCMOS on SOI VIP50	0.5	3	1	5.5	Sep-06
National Semiconductor	LM5115	CTR-0606-903	BiCMOS	1.5	2	1	30	Jun-06
STMicroelectronics	4376441_SAR	SAR-0605-901	BCD (BCD5/BCD6)	0.6	4	1		May-06
Freescale	MRF6P3300H	PPR-0604-801	RF-LDMOS	0.60	2	1		Apr-06
STMicroelectronics	4376441_CTR	CTR-0604-902	BCD5 (Likely)	0.6	4	1		Apr-06
Texas Instruments	TPS62110	PPR-0603-801	LBC 7 Bipolar, CMOS DMOS (BCD)	0.25	3+RDL	2	17	Mar-06
STMicroelectronics	ST1S03	PPR-0601-801	BCD6	0.35	3	1	16	Jan-06
STMicroelectronics	STA323W_CUD63A	CTR-0510-901	BCD MOS (CUD63A)	1.5	3	2	36	Oct-05
STMicroelectronics	STA323W_V465AA	CTR-0510-901	CMOS (V465AA)	0.25	6	1	36	Oct-05
Maxim	MAX8724E	CTR-0508-901	BiCMOS	1	2	2	17.6	Aug-05
Texas Instruments	TAS5111DAD	PPR-0508-801	LBC5 Bipolar, CMOS DMOS (BCD)	0.35	2+RDL	2		Aug-05
Infineon	SIGC158T120R3	PPR-0507-902	Bipolar IGBT	N/A	2	1	1200	Jul-05
Maxim	MAX8585	CTR-0506-902	BiCMOS	1	2	2	12	Jun-05
PowerDsine	PD64004	PPR-0504-001	SMOS8MV (Freescale)	0.25	4	1	80	Apr-05
Infineon	SPP02N80C3	PPR-0503-001	MOS	N/A	1	1	800	Mar-05
Linear Technologies	LTC4267 3803	CTR-0502-001	BiCMOS	N/A	2	1	-	Feb-05
Linear Technologies	LTC4267 4257B1	CTR-0502-001	BCD	N/A	1	1	-	Feb-05
National Semiconductor	LM5070M-TC50	CTR-0502-004	BiCMOS	N/A	2	1	6.6	Feb-05
National Semiconductor	LM5102	CTR-0410-002	BiCMOS	1.5	2	1	14	Oct-04
Texas Instruments	TPS2375	CTR-0410-005	BiCMOS	N/A	2	1	12	Oct-04
Texas Instruments	TPS2375	CTR-0410-005	BiCMOS	N/A	2	1	12	Oct-04

[Please contact us for any inquiries](#)